



450V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C	
-450V	21Ω @ V _{GS} = -10V	-0.6A	

Description

This 450V enhancement mode P-channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of Telecom and general high-voltage switching circuits.

Applications

- Load Switching
- Uninterrupted Power Supply

Features and Benefits

- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

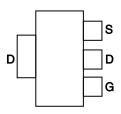
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

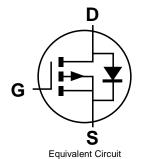
SOT223



Top View



Pin Out - Top View



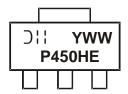
Ordering Information (Note 4)

Part Number Qualification		Case	Packaging	
	DMP45H21DHE-13	Standard	SOT223	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



O!! = Manufacturer's Marking P450HE = Marking Code YWW = Date Code Marking Y or Y= Year (ex: 7 = 2017) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-450	V	
Gate-Source Voltage	V_{GSS}	±30	V	
Continuous Prain Current (Note 6) V 10V	T _C = +25°C	Ι _D	-0.6	Α
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +70$		Ι _D	-0.4	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)(Note5)	I _{DM}	-1.2	Α	
Maximum Body Diode Continuous Current (Note5)	Is	-0.9	Α	
Avalanche Energy (Note 8) L=60mH	E _{AS}	30	mJ	
Avalanche Current (Note 8) L=60mH	I _{AS}	-1	Α	
Peak Diode Recovery dv/dt (I _{SD} ≤ 1.0A, di/dt ≤ 100A/µs)	dv/dt	26	V/ns	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)	TC = +25°C	0	12.5	W	
Total Power Dissipation (Note 6)	TC = +70°C	P_{D}	8	l vv	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ heta JA}$	108	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{eJC}	10	°C/W	
Operating and Storage Temperature Range		T_J, T_STG	-55 to +150	°C	

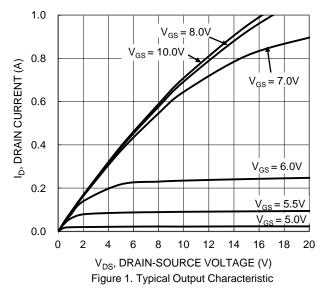
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

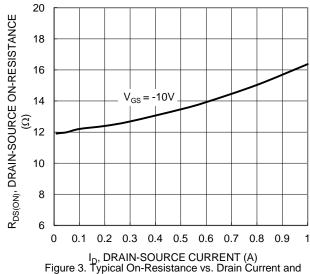
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	-450	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -450V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	-3.0	-4	-5.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		13	21	Ω	$V_{GS} = -10V, I_D = -0.3A$	
Diode Forward Voltage	V_{SD}	_	-0.84	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	1,003	_			
Output Capacitance	Coss		25.5	_	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Reverse Transfer Capacitance	Crss		2.3	_			
Gate Resistance	R_G	_	615	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Q_g	_	4.2	_		V _{DS} = -225V, I _D = -1A, V _{GS} = -10V	
Gate-Source Charge	Qgs	_	1.1	_	nC		
Gate-Drain Charge	Q_{gd}	_	2.1	_			
Turn-On Delay Time	t _{D(ON)}	_	17	_		V_{DD} = -225V, R_G = 3.0Ω , I_D = -1A	
Turn-On Rise Time	t _R	_	22	_			
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns		
Turn-Off Fall Time	t _F	_	21	_			
Body Diode Reverse Recovery Time	t _{RR}	_	113	_	ns	$V_{GS} = 0V$, $V_{DD} = -200V$, $I_{S} = -1A$, $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge	Q _{RR}		540	_	nC	$V_{GS} = 0V$, $V_{DD} = -200V$, $I_{S} = -1A$, $di/dt = 100A/\mu s$	

Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







Gate Voltage

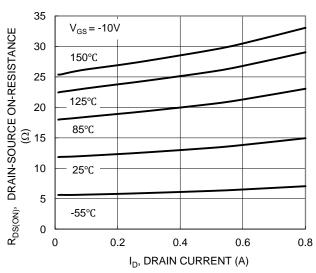


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

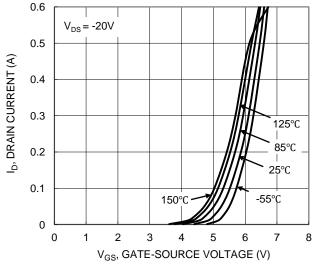


Figure 2. Typical Transfer Characteristic

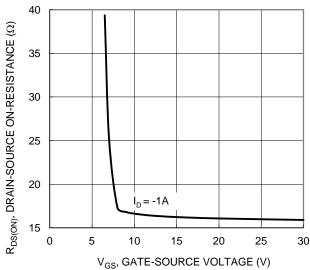


Figure 4. Typical Transfer Characteristic

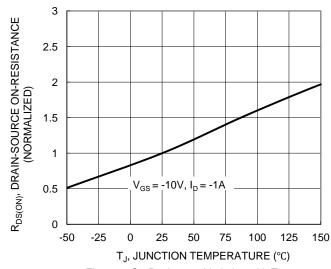


Figure 6. On-Resistance Variation with Temperature



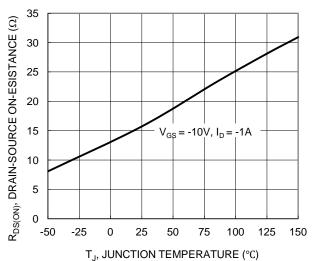


Figure 7. On-Resistance Variation with Temperature

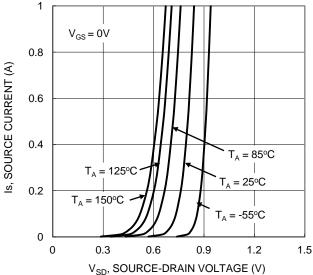
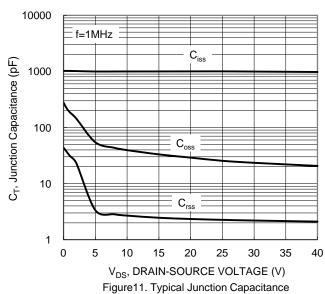


Figure 9. Diode Forward Voltage vs. Current



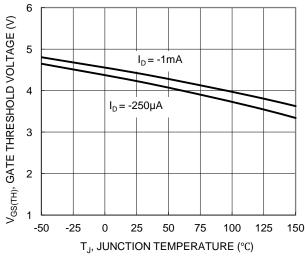


Figure 8. Gate Threshold Variation vs. AmbientTemperature

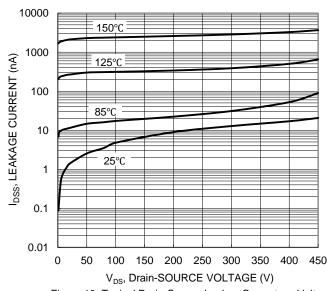


Figure 10. Typical Drain-Source Leakge Current vs. Voltage

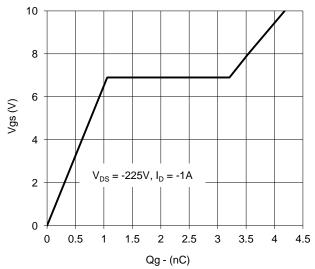


Figure 12. Gate Charge



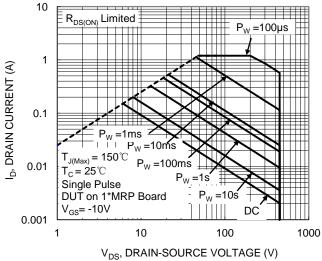


Figure 13. SOA, Safe Operation Area

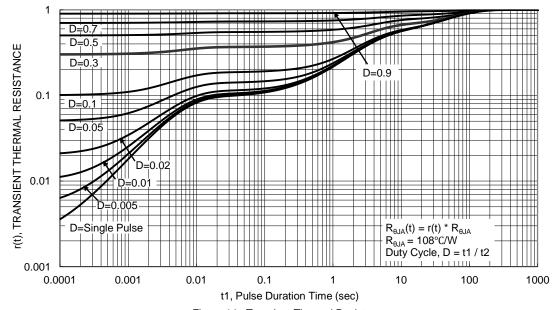


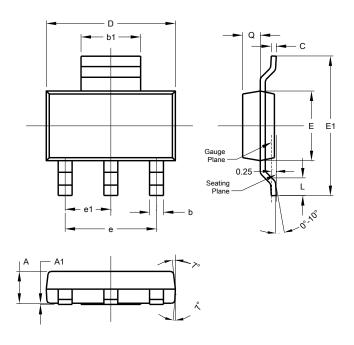
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

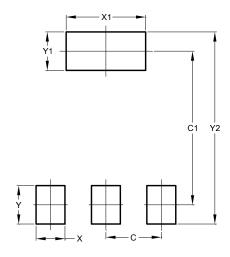


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
V2	8 00



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